

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,018,939 B2
DATED : March 28, 2006
INVENTOR(S) : S. Harma

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 10,

Line 29, should read as follows:

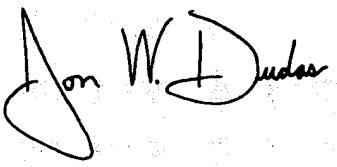
17. A method for making a semiconductor device, comprising the steps of:
 providing a semiconductor substrate;
 etching a plurality of openings in the semiconductor substrate such that, upon completion of the etch,
 at least some of the opening have an organometallic processing residue disposed on a surface
 thereof, the processing residue having been formed during the etching process; and
 removing at least a portion of the processing residue by contacting the processing residue with a
 micellar solution;
 wherein the micellar solution comprises, by weight, about 0.01% to about 1% hydrocarbon surfactant, about 1% to about 10% citric acid, and about 1% to about 10% oxalic acid.

Line 41, should read as follows:

18. The method of claim 17, wherein the micellar solution further comprises, by weight, about 0.01% to about 1% hydrocarbon surfactant, about 1% to about 10% citric acid, about 1% to about 10% oxalic acid, and about 1% to about 10% ethylene glycol monobutyl ether (EGMBE).

Signed and Sealed this

Thirtieth Day of May, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office